

Electronic Supplementary Material

Investigation on characteristics of the graphene film on various crystal planes of polycrystalline aluminum nitride

Jiahao Wang^{1,2}, Lipiao Bao¹, Jianxun Xu (✉)², and Xing Lu (✉)¹

1 State Key Laboratory of Materials Processing and Die & Mould Technology, School of Materials Science and Engineering, Huazhong University of Science and Technology, Wuhan 430074, China

2 CAS Key Laboratory for Biomedical Effects of Nanomaterials and Nanosafety, National Center for Nanoscience and Technology, Beijing 100190, China

E-mails: xujx@nanoctr.cn (J.X.); lux@hust.edu.cn (X.L.)

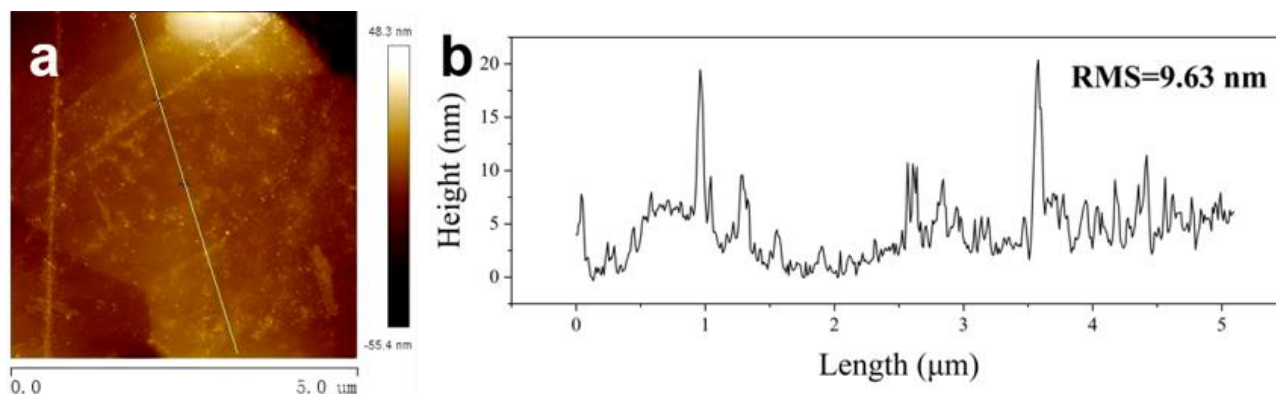


Fig. S1 (a) Height topography of an AFM image. (b) Height profile along the white path in Panel (a).

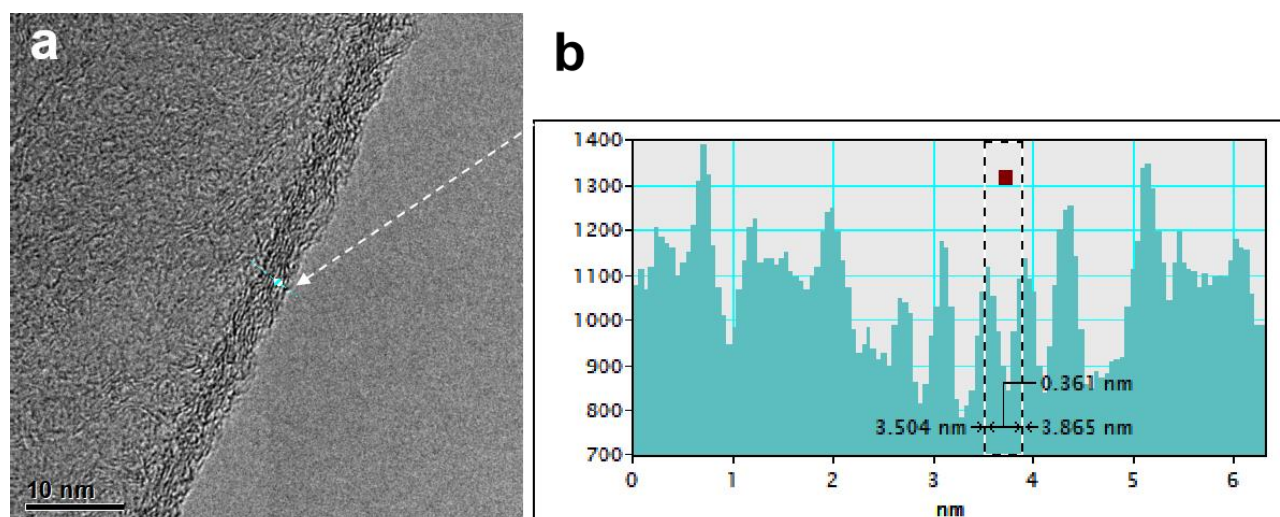


Fig. S2 (a) HR-TEM image of the graphene film prepared by SEMI quenching on the surface of polycrystalline AlN. (b) In the corresponding area, the spacing of the crystal surface is analyzed, and the spacing of the crystal surface is 0.361 nm.